# RGW40TK65D

## 650V 20A Field Stop Trench IGBT

Datasheet

V <sub>CES</sub>	650V
I <sub>C (100°C)</sub>	16A
V <sub>CE(sat) (Typ.)</sub>	1.5V
$P_{D}$	61W

# Outline TO-3PFM

## Features

- 1) Low Collector Emitter Saturation Voltage
- 2) High Speed Switching
- 3) Low Switching Loss & Soft Switching
- 4) Built in Very Fast & Soft Recovery FRD
- 5) Pb free Lead Plating; RoHS Compliant

## Application

**PFC** 

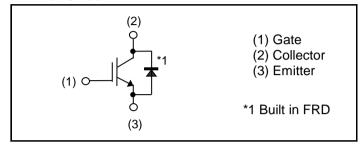
**UPS** 

Welding

Solar Inverter

ΙH

## ●Inner Circuit



●Packaging Specifications

Trackaging Specifications					
Packaging	Tube				
Reel Size (mm)	-				
Tape Width (mm)	-				
Basic Ordering Unit (pcs)	450				
Packing Code	C11				
Marking	RGW40TK65D				
	Packaging Reel Size (mm) Tape Width (mm) Basic Ordering Unit (pcs) Packing Code				

## ● Absolute Maximum Ratings (at T<sub>C</sub> = 25°C unless otherwise specified)

Parameter		Symbol	Value	Unit
Collector - Emitter Voltage	ollector - Emitter Voltage		650	V
Gate - Emitter Voltage		$V_{GES}$	±30	V
Callactar Current	T <sub>C</sub> = 25°C	I <sub>C</sub>	27	Α
Collector Current	T <sub>C</sub> = 100°C	I <sub>C</sub>	16	Α
Pulsed Collector Current	Pulsed Collector Current		80	Α
Diode Forward Current	T <sub>C</sub> = 25°C	I <sub>F</sub>	27	А
	T <sub>C</sub> = 100°C	I <sub>F</sub>	16	Α
Diode Pulsed Forward Current	•	I <sub>FP</sub> *1	80	Α
Power Dissipation	T <sub>C</sub> = 25°C	P <sub>D</sub>	61	W
	T <sub>C</sub> = 100°C	P <sub>D</sub>	30	W
Operating Junction Temperature	-	T <sub>j</sub>	-40 to +175	°C
Storage Temperature		T <sub>stg</sub>	-55 to +175	°C

<sup>\*1</sup> Pulse width limited by T<sub>jmax.</sub>

## ●Thermal Resistance

Parameter	Symbol	Values			Unit
Farameter		Min.	Тур.	Max.	Offic
Thermal Resistance IGBT Junction - Case	$R_{\theta(j-c)}$	-	-	2.44	°C/W
Thermal Resistance Diode Junction - Case	R <sub>θ(j-c)</sub>	-	-	2.79	°C/W

## ●IGBT Electrical Characteristics (at T<sub>i</sub> = 25°C unless otherwise specified)

Parameter	Symbol	Conditions	Values			Unit
r arameter	Symbol	Conditions	Min.	Тур.	Max.	Offic
Collector - Emitter Breakdown Voltage	BV <sub>CES</sub>	$I_{C} = 10 \mu A, V_{GE} = 0 V$	650	ı	ı	V
Collector Cut - off Current	I <sub>CES</sub>	$V_{CE} = 650V, V_{GE} = 0V$	ı	1	10	μΑ
Gate - Emitter Leakage Current	I <sub>GES</sub>	$V_{GE} = \pm 30V, V_{CE} = 0V$	ı	ı	±200	nA
Gate - Emitter Threshold Voltage	$V_{GE(th)}$	$V_{CE} = 5V, I_{C} = 13.3 \text{mA}$	5.0	6.0	7.0	V
Collector - Emitter Saturation Voltage	V <sub>CE(sat)</sub>	$I_{C} = 20A, V_{GE} = 15V,$ $T_{j} = 25^{\circ}C$ $T_{j} = 175^{\circ}C$	-	1.5 1.85	1.9 -	V

# ●IGBT Electrical Characteristics (at T<sub>j</sub> = 25°C unless otherwise specified)

Parameter	Symbol	Conditions	Values			Unit
Parameter			Min.	Тур.	Max.	Offic
Input Capacitance	C <sub>ies</sub>	$V_{CE} = 30V$ ,	-	1680	-	
Output Capacitance	C <sub>oes</sub>	$V_{GE} = 0V$ ,	-	47	-	pF
Reverse transfer Capacitance	C <sub>res</sub>	f = 1MHz	-	31	-	
Total Gate Charge	$Q_g$	V <sub>CE</sub> = 400V,	-	59	-	
Gate - Emitter Charge	$Q_{ge}$	$I_{\rm C} = 20A$ ,	-	13	-	nC
Gate - Collector Charge	$Q_{gc}$	$V_{GE} = 15V$	-	23	-	
Turn - on Delay Time	t <sub>d(on)</sub>		-	33	-	
Rise Time	t <sub>r</sub>	$I_C = 20A, V_{CC} = 400V,$ $V_{GF} = 15V, R_G = 10\Omega,$	-	10	-	ns
Turn - off Delay Time	t <sub>d(off)</sub>	$T_i = 25^{\circ}C$	-	76	-	
Fall Time	t <sub>f</sub>	Inductive Load *E <sub>on</sub> include diode reverse recovery	-	63	-	
Turn - on Switching Loss	E <sub>on</sub>		-	0.33	-	mJ
Turn - off Switching Loss	E <sub>off</sub>		-	0.30	-	
Turn - on Delay Time	t <sub>d(on)</sub>		-	31	-	
Rise Time	t <sub>r</sub>	$I_C = 20A$ , $V_{CC} = 400V$ , $V_{GE} = 15V$ , $R_G = 10\Omega$ , $T_j = 175^{\circ}C$ Inductive Load *E <sub>on</sub> include diode reverse recovery	-	10	-	ns
Turn - off Delay Time	t <sub>d(off)</sub>		-	102	-	
Fall Time	t <sub>f</sub>		-	76	-	
Turn - on Switching Loss	E <sub>on</sub>		-	0.34	-	mJ
Turn - off Switching Loss	E <sub>off</sub>		-	0.43	-	IIIJ
Reverse Bias Safe Operating Area	RBSOA	$I_C = 80A$ , $V_{CC} = 520V$ , $V_P = 650V$ , $V_{GE} = 15V$ , $R_G = 100\Omega$ , $T_j = 175^{\circ}C$	FU	LL SQUA	RE	-

# **•FRD Electrical Characteristics** (at $T_j = 25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Conditions	Values			Unit
raiaillelei	Symbol		Min.	Тур.	Max.	Offic
		$I_F = 20A$ ,				
Diode Forward Voltage	$V_{F}$	T <sub>j</sub> = 25°C	-	1.45	1.9	V
		T <sub>j</sub> = 175°C	-	1.55	-	
Diode Reverse Recovery Time	t <sub>rr</sub>		-	92	-	ns
Diode Peak Reverse Recovery Current	I <sub>rr</sub>	I <sub>F</sub> = 20A, V <sub>CC</sub> = 400V,	-	6.7	ı	А
Diode Reverse Recovery Charge	Q <sub>rr</sub>	di <sub>F</sub> /dt = 200A/µs, T <sub>j</sub> = 25°C	-	0.34	-	μC
Diode Reverse Recovery Energy	Err		-	14.1	-	μJ
Diode Reverse Recovery Time	t <sub>rr</sub>	$I_F = 20A,$ $V_{CC} = 400V,$ $di_F/dt = 200A/\mu s,$ $T_j = 175^{\circ}C$	-	123	-	ns
Diode Peak Reverse Recovery Current	I <sub>rr</sub>		-	7.8	1	А
Diode Reverse Recovery Charge	Q <sub>rr</sub>		_	0.59	-	μC
Diode Reverse Recovery Energy	E <sub>rr</sub>			30.7	-	μJ

## •Electrical Characteristic Curves

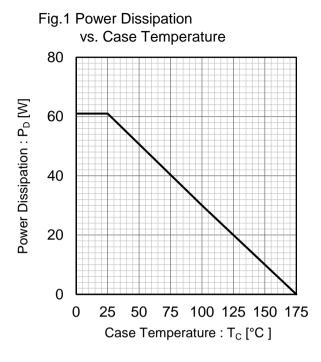


Fig.3 Forward Bias Safe Operating Area

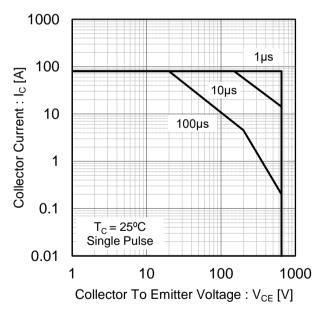
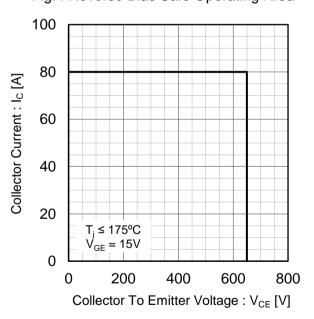


Fig.4 Reverse Bias Safe Operating Area



## • Electrical Characteristic Curves

Fig.5 Typical Output Characteristics

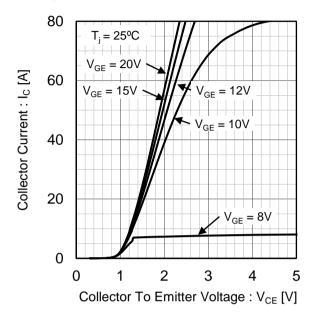


Fig.6 Typical Output Characteristics

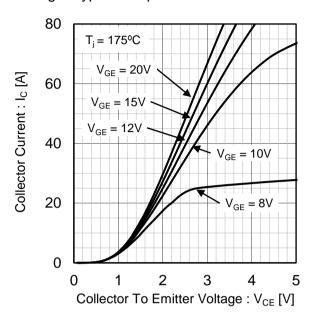


Fig.7 Typical Transfer Characteristics

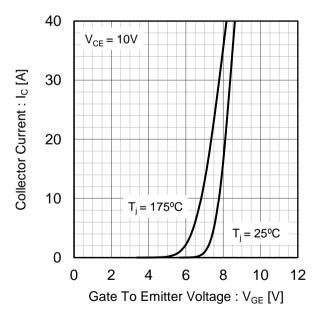
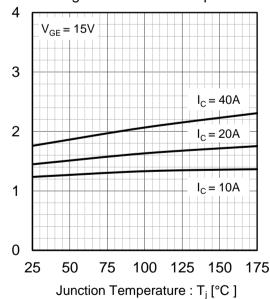


Fig.8 Typical Collector to Emitter Saturation Voltage vs. Junction Temperature



Collector To Emitter Saturation

Voltage: V<sub>CE(sat)</sub> [V]



#### Electrical Characteristic Curves

Fig.9 Typical Collector to Emitter Saturation Voltage vs. Gate to Emitter Voltage 20  $T_i = 25^{\circ}C$ Collector To Emitter Saturation  $I_C = 40A$ 15  $I_C = 20A$ Voltage: V<sub>CE(sat)</sub> [V]  $I_C = 10A$ 10 5 0 5 10 15 20 Gate To Emitter Voltage: VGE [V]

Fig.10 Typical Collector to Emitter Saturation Voltage vs. Gate to Emitter Voltage

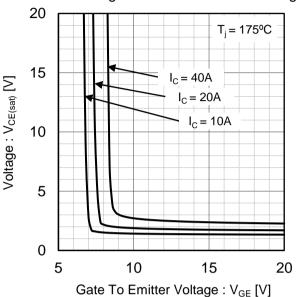


Fig.11 Typical Switching Time vs. Collector Current 1000 Switching Time [ns]  $t_{d(off)}$ 100  $t_{d(on)}$ 10  $V_{CC} = 400V$ ,  $V_{GE} = 15V$ ,  $R_G = 10\Omega$ ,  $T_j = 175^{\circ}C$ Inductive load 1 0 10 20 30 40 Collecter Current : I<sub>C</sub> [A]

Fig.12 Typical Switching Time vs. Gate Resistance 1000 Switching Time [ns]  $t_{d(off)}$ 100  $t_{d(on)}$ 10  $V_{CC}$  = 400V,  $V_{GE}$  = 15V,  $I_{C}$  = 20A,  $T_{j}$  = 175°C Inductive load 1 0 10 20 30 40 50 Gate Resistance :  $R_G[\Omega]$ 

Collector To Emitter Saturation

## Electrical Characteristic Curves

 $\mathsf{E}_{\mathsf{off}}$ 

 $\mathsf{E}_{\mathsf{on}}$ 

10

0.1

0.01

0

Fig.13 Typical Switching Energy Losses vs. Collector Current 10 Switching Energy Losses [mJ] 1

 $V_{CC} = 400V, V_{GE} = 15V,$   $R_G = 10\Omega, T_j = 175^{\circ}C$ 

Inductive load

30

40

20

Collecter Current : I<sub>C</sub> [A]

Fig.14 Typocal Switching Energy Losses vs. Gate Resistance

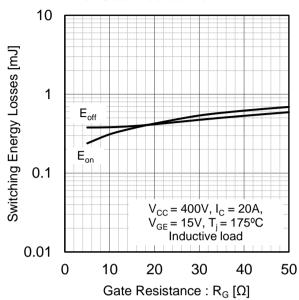


Fig.15 Typical Capacitance vs. Collector to Emitter Voltage

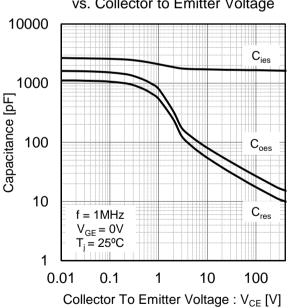
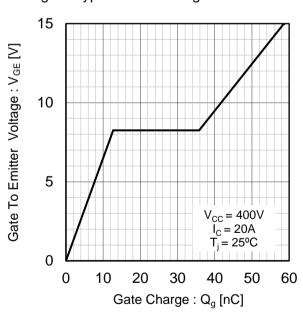


Fig.16 Typical Gate Charge



#### ● Electrical Characteristic Curves

Fig.17 Typical Diode Forward Current vs. Forward Voltage

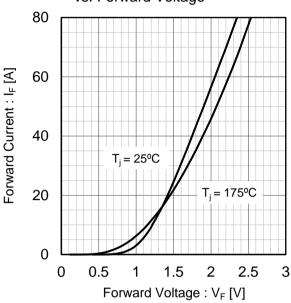


Fig.18 Typical Diode Revese Recovery Time vs. Forward Current

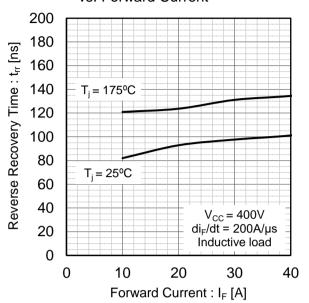


Fig.19 Typical Diode Reverse Recovery Current vs. Forward Current

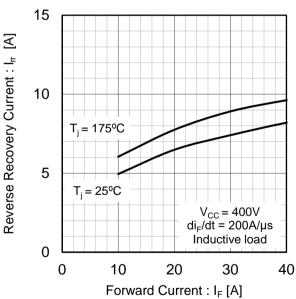
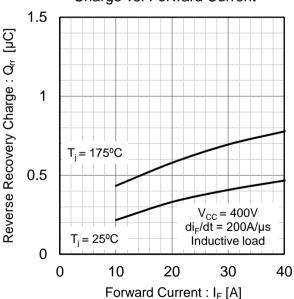


Fig.20 Typical Diode Rrverse Recovery Charge vs. Forward Current



## • Electrical Characteristic Curves

Fig.21 Typical IGBT Transient Thermal Impedance

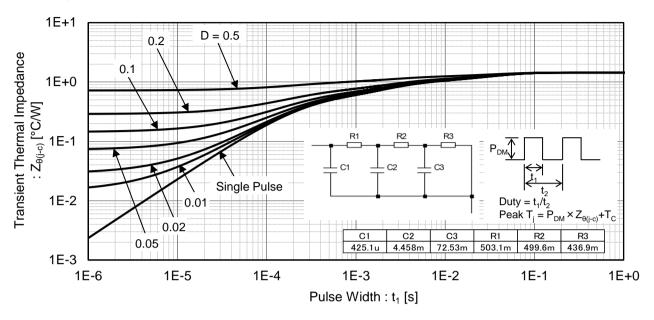
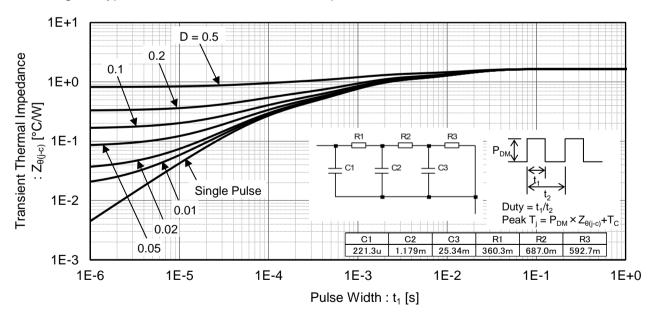


Fig.22 Typical Diode Transient Thermal Impedance



## ●Inductive Load Switching Circuit and Waveform

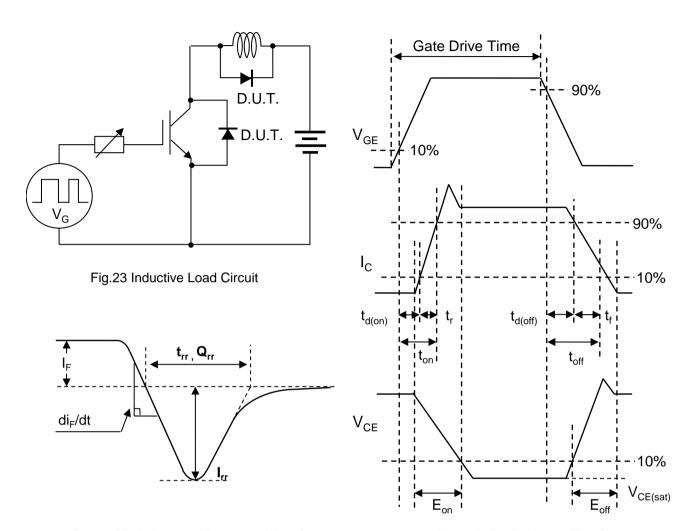


Fig.25 Diode Reverse Recovery Waveform

Fig.24 Inductive Load Waveform

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